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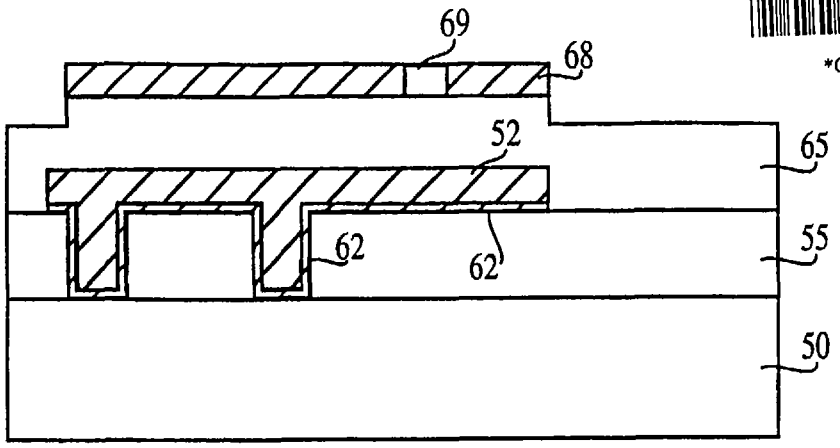
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(54) Title: SUBSTRACTIVE METALLIZATION STRUCTURE AND METHOD OF MAKING

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(57) Abstract: A substractive metallization structure with a plurality of low dielectric constant insulating layers (55, 65) acting as etch stops is disclosed. The selected low dielectric constant materials have similar methods of formation and similar capacities to wishtand physical and thermal stress. In addition, the etchant used for each low dielectric constant insulating layer has a very small etching rate relative to the other low dielectric constant insulating layers.

WO 02/019419 A3